REMARKS

Reconsideration of the above-referenced application in view of the above amendment, and of the following remarks, is respectfully requested.

Claims 1-8 are pending in this case. Claims 9-16 are canceled herein.

The Examiner rejected claims 1, 2, 6 and 7 under 35 U.S.C. § 102(e) as being anticipated by Saia et al. (U.S. Pat. No. 5,874,770).

Applicant respectfully submits that claim 1 is unanticipated by Saia et al as there is no disclosure or suggestion in Saia of an integrated circuit having a thin film resistor, much less an integrated circuit having a thin film resistor located between an upper and lower metal interconnect layer. Saia teaches forming resistors 28. However, resistors 28 are not part of the integrated circuit 44. Saia teaches a flexible interconnect film to which an integrated circuit chip can be attached. The integrated circuit 44 does not comprise the thin film resistors 28 as required by the claim. Accordingly, Applicant respectfully submits that claim 1 and the claims dependent thereon are unanticipated by Saia et al.

The Examiner rejected claim 3 under 35 U.S.C. §103(a) as being unpatentable over Saia et al. (U.S. Pat. No. 5,874,770).

Applicant respectfully submits that claim 3 is patentable over Saia et al for the same reason discussed above relative to claim 1 from which claim 3 depends.

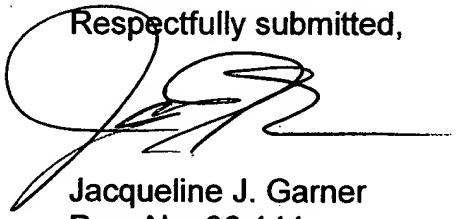
The Examiner rejected claims 4, 5 and 8 under 35 U.S.C. §103(a) as being unpatentable over Saia et al. as applied to claim 1, and further in view of Linn et al. (U.S. Patent No. 5,547,896).

Applicant respectfully submits that claim 4, 5, and 8 are patentable over Saia et al in view of Linn et al as there is no disclosure or suggestion in the references of an integrated circuit having a thin film resistor located within a multilevel dielectric layer between an upper and lower metal interconnect layer. As discussed above, Saia does not teach an integrated circuit comprising a thin film resistor. Linn et al is added by the Examiner to teach a hardmask layer comprising TiW or TiN and to teach a resistor material of NiCr. Linn's thin film resistor is formed as part of a semiconductor device. However, there is no disclosure or suggestion in the references for an integrated circuit having a thin film resistor located between an upper and a lower metal interconnect layer of the integrated circuit. Accordingly, Applicant respectfully submits that claims 4, 5, and 8 are patentable over the references.

The other references cited by the Examiner have been reviewed but are not felt to come within the scope of the claims as amended.

In light of the above, Applicant respectfully requests withdrawal of the Examiner's rejections and allowance of claims 1-8. If the Examiner has any questions or other correspondence regarding this application, Applicant requests that the Examiner contact Applicant's attorney at the below listed telephone number and address.

Respectfully submitted,



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